

Analytical Approach For Decoder Delay Reduction Sec-DED-DAEC Codes Derived From Orthogonal Latin Square Codes

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Abstract

Although tremendous progress has done in past years on memory designing but still Radiation-induced soft errors is concerned area in the field of soft memories and the single error correction double error detection (SEC-DED) codes are commonly used to give assured memory contents with absence of corrupted scenario. Since SEC-DED codes cannot correct multiple errors, they are often combined with interleaving. Interleaving, however, impacts memory design and performance and cannot always be used in small memories. This limitation has spurred interest in codes that can correct adjacent bit errors. In particular, several SEC-DED double adjacent error correction (SEC-DED-DAEC) codes have recently been proposed. Implementing DAEC has a cost as it impacts the decoder complexity and delay. Another issue is that most of the new SEC-DED-DAEC codes miscorrect some double nonadjacent bit errors. In this brief, a new class of SEC-DED-DAEC codes is derived from orthogonal Latin squares codes. The new codes significantly reduce the decoding complexity and delay. In addition, the codes do not miscorrect any double nonadjacent bit errors. The main disadvantage of the new codes is that they require a larger number of parity check bits. Therefore, they can be useful when decoding delay or complexity is critical or when miscorrection of double nonadjacent bit errors is not acceptable. The proposed codes have been implemented in Hardware Description Language and compared with some of the existing SEC-DED-DAEC codes. Finally the experimental results confirm the reduction in decoder delay.

KEYWORDS: Error correction codes, Orthogonal Latin square codes. Single error correction double error detection (SEC-DED), Double adjacent error correction (DAEC), Memory

1. INTRODUCTION

Memories are very dense structures that are especially susceptible to defects. Transient errors due to radiation, power supply noise, etc., can cause bit-flips in a memory. To protect the data integrity of the memory during runtime operations, error correcting codes (ECC) of various class and strength is generally employed. A soft error occurs when a radiation event causes enough of a charge disturbance to reverse or flip the data state of a memory cell, register, latch, or flip-flop. The error is “soft” because the circuit/device itself is not permanently damaged by the radiation—if new data are written to the bit, the device will store it correctly.

Recently, research has shown that commercial static random access memories (SRAMs) are now so small and sufficiently sensitive that single event upsets (SEUs) may be induced from the electronic stopping of a proton. This sensitivity appears near the 65 nm technology node as the critical charge to upset a cell is on the order of 1 fC; merely 6,000 electrons are required to cause a change in data state. The lower critical charge required to cause a bit-flip has more pronounced effects on space applications compared to terrestrial ones. Also low voltage operation can lead to greater number of failures, arising due to more pronounced effect of process variations. Voltage scaling, which is one of the most effective ways to reduce power consumption can lead to unreliable operations at lower voltages. Voltage scaling is

limited by a minimum value referred to as VCC min beyond which circuits may not function reliably. Voltage scaling beyond Vccmin gives rise to reliability issues, most notably for the memory sub-systems. In order for Vccmin to be reduced to enable ultra-low power modes in microprocessors and other circuits, some means for handling high memory bit failure rates is required.

To protect memories, error correction codes are commonly used. Traditionally, single error correction double error detection (SEC-DED) codes have been used. A SEC-DED code has a minimum Hamming distance of four and is able to correct single bit errors and detect double errors without miscorrection. This is important to avoid silent data corruption. SEC-DED codes are sufficient when errors affect only one bit, however, the percentage of soft errors affecting more than a single bit is increasing as technology scales. For memories implemented in 40 nm and below, multiple bit errors are a significant percentage of errors and thus SEC-DED codes alone are no longer sufficient to protect memories. One option is to combine SEC-DED codes with interleaving. Interleaving, places the bits that belong to the same logical word physically apart. As the errors caused by a radiation particle hit are physically close, this ensures that the errors affect at most one bit per logical word. Interleaving has an impact on the memory design.

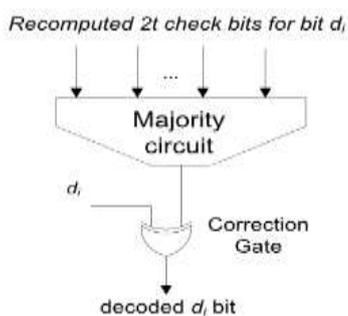


Figure 1: Illustration of OS-MLD decoding for OLS codes

Another alternative is to use error correction codes that can correct adjacent bits. In many cases, directly adjacent bits account for over 90% of the observed multiple bit errors. Several codes have been recently proposed to this end. For example, a code that can correct double and triple adjacent errors for words of 16 bit was presented. A technique to

design SEC-DED double adjacent error correction (SEC-DED-DAEC) codes was introduced. The extension of SEC-DED-DAEC codes to also detect larger burst errors has also been recently considered. One issue with those SEC-DED-DAEC codes is that they can miscorrect some double nonadjacent bit errors. The reduction of the miscorrection probability has been considered. The algorithm tries to minimize the number of 4 cycles. It was shown that miscorrection can be avoided for the most common error patterns and in some cases for all patterns at the cost of adding additional parity check bits. Another issue with SEC-DED-DAEC codes is that their decoding complexity and latency are larger than those of SEC-DED codes.

The main limitation for these codes is that they require a number of parity check bits equal to the number of data bits. The use of more advanced codes such as difference set and orthogonal Latin squares (OLS) codes to correct adjacent errors has also been considered. Those codes are one-step majority logic decodable (OS-MLD) and therefore, can be decoded with low latency. In this brief, a new class of SEC-DED-DAEC codes is presented. The proposed codes are derived from OLS codes. They require fewer parity check bits than double error correction (DEC) OLS codes and are simpler to decode. Compared with existing SEC-DED-DAEC codes, the new codes have two main advantages: first, there is no miscorrection for double nonadjacent errors and second, the decoding is much simpler and faster. The main drawback for the proposed codes is that they require more parity check bits than existing SEC-DED-DAEC codes. Therefore, the proposed codes can be useful to protect memories in which decoding latency is critical or miscorrection cannot be tolerated. The rest of this brief is organized as follows.

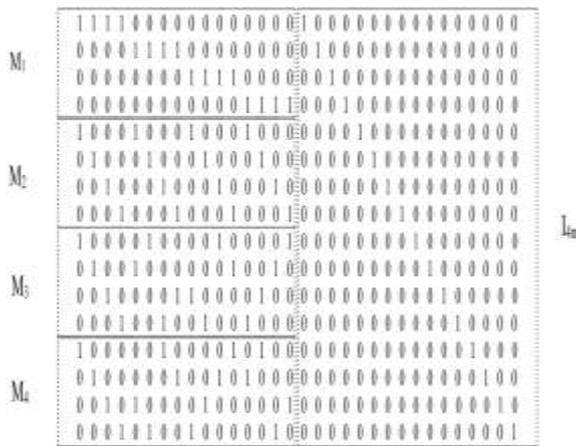


Figure 2: Parity check matrix H for the OLS code with $k=16$ and $t=2$

2. ERROR CORRECTING CODES

The most common error correcting code that is used is single-error-correcting, double-error-detecting (SEC-DED) codes. These codes can correct single bit errors in any word of the memory and can detect double bit errors, have moderate redundancy in terms of check bits and are relatively easy to decode. Decoding and correction are done via syndrome method which takes single cycle. A special class of SEC-DED codes known as Hsiao codes [Hsiao 70] was proposed to improve the speed, cost, and reliability of the decoding logic. However some situations demand more stringent reliability requirements, thus necessitating error correction stronger than normal SEC-DED.

Stronger error correcting codes includes single byte-error-correcting, double-byte error-detecting (SBC-DBD) codes. These codes perform at a higher order Galois field and consequently the encoding and decoding are more complex. Moreover, they require more check bits thereby increasing the size of the memory. There are also the double-error-correcting triple-error-detecting (DEC-TED) codes, which come at the cost of much larger overhead in terms of both the check bits and more complex hardware to implement the error correction and detection. The general drawbacks with these methods are latency and speed. Most of these codes require several cycles to correct the first error unlike the SEC-DED codes. Moreover, the encoding and decoding are much more complex and require several table lookups for multiplication

in higher order fields. However in spite of their low check bits overhead and single cycle decoding, SEC-DED codes are not able to provide requisite reliability under certain conditions.

3. OLS CODES

The OLS codes were introduced decades ago to protect memories. On the end simultaneously have recently been proposed to protect caches and interconnects. The block sizes for OLS codes are $k=m/2$ data bits and $2tm$ parity bits. Where t is the number of errors that the code can correct and m is an integer. For memories, the word sizes are typically a power of two and therefore m is commonly also power of two. The main advantage of OLS codes is that their decoding is simple and fast. This is because, as mentioned in the introduction, OLS codes can be decoded using OS-MLD. In OS-MLD, each bit is decoded by simply taking the majority value on the set of the recomputed parity check equations (or syndrome bits) in which it participates. The idea behind OS-MLD is that when an error occurs in bit d_i , the recomputed parity checks in which it participates will take a value of one unless there are errors in other bits. Therefore, a majority of ones in those recomputed checks is an indication that the bit is in error and therefore needs to be corrected. If the code is such that two bits share at most one parity check, then $t-1$ errors on other bits will not affect the majority of the $2t$ vote and therefore, the error will be corrected. Only a few codes have this property and can be decoded using OS-MLD. This is the case for difference set codes and for OLS codes, as mentioned in the introduction.

More formally, the construction of OLS codes is such that:

- 1) Each data bit participates in exactly $2t$ parity check bits;
- 2) Each other data bit participates in at most one of those parity check bits.

Therefore, for a number of errors or smaller, when one error affects a given bit, the remaining $t-1$ errors can, in the worst case affect $t-1$ check bits on which that bit participates. Therefore, still a majority of $+1$ will trigger the correction on the erroneous bit. Conversely, when a given bit is correct, t errors on other bits will not cause miscorrection as a majority

detecting a nonzero even number of ones in the syndrome that can only be caused by a multiple bit error and checking if any correction has been made.

k	n-k	m
16	12	4
64	24	8
256	48	16

TABLE 2: PARAMETERS OF THE PROPOSED SEC-DED-DAEC CODES

The proposed scheme can be summarized as follows:

- 1) Reduce the H matrix of the DEC OLS code by eliminating M_1 ;
- 2) Place the bits in the groups of m bits g_1, g_2, \dots, g_m such that the bits at the borders of the groups do not share any parity check;
- 3) Interleave the parity bits with the data bits such that two adjacent bits never participate in the same parity bit;
- 4) Instead of majority voting, decode based on unanimity (three-way AND) to correct errors;
- 5) Implement the circuit of Fig. 6 to detect uncorrectable errors.

5. EXPERIMENTAL RESULTS

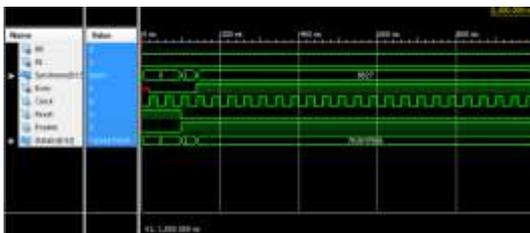


Figure 7: SIMULATION RESULT OF Error MLD test



Figure 8: SIMULATION RESULT OF OLS Encoder test

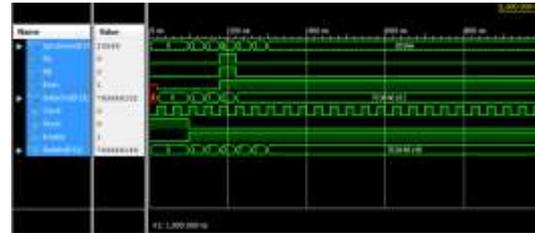


Figure 9: SIMULATION RESULT OF OLS Decoder test

6. CONCLUSION

In this brief, a new class of SEC-DED-DAEC codes has been presented. The codes are derived from DEC OLS codes and can be decoded with low latency. Another interesting feature is that the codes do not experience miscorrection when double nonadjacent error occurs. This is interesting to minimize silent data corruption. The codes can also correct some nonadjacent double errors.

Compared with existing SEC-DED-DAEC codes, they require a larger number of parity check bits, therefore, they are attractive when low latency decoding is a required. The codes have been implemented in HDL and the resulting implementations compared with existing SEC-DED-DAEC codes to put the reductions in decoding latency in perspective. The ideas used to derive the proposed SEC-DED-DAEC can also be used to derive burst error correction codes from OLS codes that can correct multiple errors. The key observation is that the structure of OLS codes is such that the data bits can be divided in groups of m bits that do not share any parity check. Therefore, any error affecting up to $2t-1$ bits in one of these groups can be corrected. This can be exploited by carefully placing the data and parity check bits so that, in the best case, up to $2t-1$ adjacent bit errors can be corrected. The development of burst error correction codes is an interesting

avenue to continue and extend the work presented in this brief.

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